L Number	Hits	Search Text	DB	Time stamp
- Number	6	(("5637884") or ("5811324")).PN.	USPAT; US-PGPUB;	2003/06/16 15:17
_	6	(("4979014") or ("5466621")).PN.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/07
-	382	(257/900).CCLs.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/07 14:39
-	378	((257/900).CCLS.) and @ad<=20000731	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/02/26 09:35
-	234007	(("257") or ("438")).CLAS.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/07 14:44
-	682	(((257/\$) or (438/\$)).CCLS.) and @ad<=20000731 and 'convex' with 'layer'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/07 14:49
_	1	"5095347".PN.	DERWENT; IBM_TDB USPAT	2002/05/07
-	1	"5095347".PN.	USPAT	14:46 2002/05/07
_	1	"5120666".PN.	USPAT	14:46 2002/05/07
-	1	"4774196".PN.	USPAT	14:46
-	1	"5410172".PN.	USPAT	14:46 2002/05/07 14:47
-	1	"5420055".PN.	USPAT	2002/05/07
-	1	"5578513".PN.	USPAT	2002/05/07 14:47
-	1	"5580802".PN.	USPAT	2002/05/07 14:48
-	610	(((257/\$) or (438/\$)).CCLS.) and @ad<=20000731 and 'convex' with 'semiconductor'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/07 14:51
-	0	(((257/\$) or (438/\$)).CCLS.) and @ad<=20000731 and 'convex semiconductor' and 'side-wall gate'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/07
-	0	(((257/\$) or (438/\$)).CCLS.) and @ad<=20000731 and 'convex semiconductor' and 'side wall gate'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/07 14:53
-	1531	(((257/\$) or (438/\$)).CCLS.) and @ad<=20000731 and 'side wall gate'	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/05/07 14:57
			EPO; JPO; DERWENT; IBM TDB	

_	40	(((((257/\$) or (438/\$)).CCLS.) and @ad<=20000731 and 'side wall gate') and	USPAT; US-PGPUB;	2002/05/07 15:09
		'convex'	EPO; JPO;	13.09
			DERWENT; IBM TDB	,
-	238	(257/394).CCLS.	USPAT;	2002/05/07
	:		US-PGPUB; EPO; JPO;	15:12
			DERWENT;	
_	232	(257/394).ccls. and @ad<=20000731	IBM_TDB USPAT;	2002/05/07
	232	(237/354):0013. and gadv-2000731	US-PGPUB;	15:43
			EPO; JPO; DERWENT;	
	-		IBM_TDB	
	1	"4979014".PN.	USPAT	2002/05/07
-	1	"5463241".PN.	USPAT	2002/05/07 15:30
_	1	"5512770".PN.	USPAT	2002/05/07
_	156	(257/262).ccls. and @ad<=20000731	USPAT;	15:31 2002/05/07
	100		US-PGPUB;	15:56
	:		EPO; JPO; DERWENT;	
	17	'trench isolated transistor'	IBM_TDB USPAT;	2002/05/07
	17	trench isolated transistor	US-PGPUB;	15:57
			EPO; JPO; DERWENT;	
	_		IBM_TDB	
-	17	trench adj isolated adj transistor	USPAT; US-PGPUB;	2004/02/24
			EPO; JPO;	
			DERWENT; IBM TDB	
-	1	"4449285".PN.	USPĀT	2002/05/07 15:59
_	1	"4606011".PN.	USPAT	2002/05/07 15:59
-	1	"4670768".PN.	USPAT	2002/05/07 15:59
-	1	"4449285".PN.	USPAT	2002/05/07
-	1	"4606011".PN.	USPAT	2002/05/07
-	1	"4670768".PN.	USPAT	2002/05/07
-	1	"4801988".PN.	USPAT	2002/05/07
-	1	"4833516".PN.	USPAT	2002/05/07 16:11
-	1	"4910567":PN.	USPAT	2002/05/07 16:11
_	1	"5013679".PN.	USPAT	2002/05/07 16:12
-	1	"5013679".PN.	USPAT	2002/05/07 16:12
_	1	"5264716".PN.	USPAT	2002/05/07 16:12
-	1	"5289027".PN.	USPAT	2002/05/07
-	1	"5348905".PN.	USPAT	2002/05/07 16:13
-	1	"5360758".PN.	USPAT	2002/05/07 16:13
-	1	"5404037".PN.	USPAT	2002/05/07
-	1	"5567962".PN.	USPAT	2002/05/07
_	1	"5567962".PN.	USPAT	2002/05/07 16:13
				

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	T	Lure cooper	T ====	1 0000 /6- /
-	1	"5567962".PN.	USPAT	2002/05/07 16:14
_	1	"5675164".PN.	USPAT	2002/05/07
-	1	"5909044".PN.	USPAT	2002/05/07
_	1	"5990510".PN.	USPAT	16:15 2002/05/07
_	1	"5994197".PN.	USPAT	16:15 2002/05/07
_	1	"5994729".PN.	USPAT	16:15 2002/05/07
_	1	"5998820".PN.	USPAT	16:15 2002/05/07 16:16
-	1	"5998821".PN.	USPAT	16:16 2002/05/07 16:16
-	1	"6008513".PN.	USPAT	2002/05/07 16:16
-	1	"6020609".PN.	USPAT	2002/05/07
-	1	"6025620".PN.	USPAT	2002/05/07 16:17
_	1	"6037210".PN.	USPAT	2002/05/07
_	2781	side adj wall adj gate	USPAT; US-PGPUB;	2002/05/07
			EPO; JPO; DERWENT;	
	46	(side adi wall adi gate) and	IBM_TDB	2002/05/07
_	46	(side adj wall adj gate) and @ad<=20000731 and 'convex'	USPAT; US-PGPUB;	16:23
			EPO; JPO; DERWENT;	
_	80	 'side-wall' adj gates	IBM_TDB USPAT;	2002/05/07
	' '		US-PGPUB;	16:27
			EPO; JPO; DERWENT;	
_	77	 ('side-wall' adj gates) and @ad<=20000731	<pre>IBM_TDB USPAT;</pre>	2002/05/07
			US-PGPUB; EPO; JPO;	16:43
			DERWENT; IBM TDB	
_	24	'convex semiconductor layer'	USPAT;	2002/05/08
			US-PGPUB; EPO; JPO;	07:58
			DERWENT; IBM TDB	
_	24	'convex semiconductor layer'	USPAT; US-PGPUB;	2004/02/24
			EPO; JPO;	10.50
			DERWENT; IBM TDB	
-	1	"3278789".PN.	USPAT	2002/05/08 08:10
-	1	"3663857".PN.	USPAT	2002/05/08 08:10
-	1	"3735186".PN.	USPAT	2002/05/08 08:10
-	1	"4093562".PN.	USPAT	2002/05/08 08:10
-	1	"4325084".PN.	USPAT	2002/05/08 08:10
-	1	"5066883".PN.	USPAT	2002/05/08 08:11
-	1	"3805123".PN.	USPAT	2002/05/08
_	1	"5753966".PN.	USPAT	2002/05/08
-	1	"5753966".PN.	USPAT	2002/05/08 08:12
	L	<u> </u>	l	

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		USOS CROOK PIN	r	
_	1	"5814532".PN.	USPAT	2002/05/08 08:12
_	1	"5972730".PN.	USPAT	2002/05/08
_	1	"6037210".PN.	USPAT	2002/05/08 08:31
_	1	"6025620".PN.	USPAT	2002/05/08
-	1	"6020609".PN.	USPAT	2002/05/08
_	1	"5998821".PN.	USPAT	2002/05/08
_	155	'projection' near 'semiconductor substrate'	USPAT; US-PGPUB; EPO; JPO;	2002/05/08 08:46
			DERWENT; IBM_TDB	
_	143	('projection' near 'semiconductor substrate') and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO;	2002/05/08
	799	(257/192).ccls. and @ad<=20000731	DERWENT; IBM_TDB USPAT;	2003/06/17
	799	(257/192).CCIS. and ead(-20000731	US-PGPUB; EPO; JPO;	08:22
			DERWENT; IBM_TDB	
-	403	((257/192).ccls. and @ad<=20000731) and 'FET'	USPAT; US-PGPUB;	2002/05/08
			EPO; JPO; DERWENT; IBM TDB	·
-	201	(257/386).ccls. and @ad<=20000731	USPĀT; US-PGPUB;	2002/05/08 10:17
			EPO; JPO; DERWENT; IBM TDB	
-	244	(257/387).ccls. and @ad<=20000731	USPAT; US-PGPUB;	2002/05/08
			EPO; JPO; DERWENT;	
_	111	(257/388).ccls. and @ad<=20000731	IBM_TDB USPAT; US-PGPUB;	2002/05/08
			EPO; JPO; DERWENT;	
_	149	(257/389).ccls. and @ad<=20000731	IBM_TDB USPAT;	2002/05/08
			US-PGPUB; EPO; JPO; DERWENT;	10:37
_	259	(257/393).ccls. and @ad<=20000731	IBM_TDB USPAT;	2002/05/08
			US-PGPUB; EPO; JPO; DERWENT;	10:39
_	315	(257/346).ccls. and @ad<=20000731	IBM_TDB USPAT;	2002/05/08
			US-PGPUB; EPO; JPO;	10:43
	93	(257/395).ccls. and @ad<=20000731	DERWENT; IBM_TDB USPAT;	2002/05/08
		(25./355/.0015. and Gad-20000/31	US-PGPUB; EPO; JPO;	10:47
		(057 (07)	DERWENT; IBM_TDB	2002/05/02
_	67	(257/27).ccls. and @ad<=20000731	USPAT; US-PGPUB; EPO; JPO;	2002/05/08
			DERWENT;	
	l		1 1011 100	

	000	(257/60) 2010 4 0-4/-20000721	IIGD2#	2002/05/00
-	206	(257/69).ccls. and @ad<=20000731	USPAT; US-PGPUB;	2002/05/08
			EPO; JPO;	10.01
			DERWENT;	
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-	39	(438/247).ccls. and @ad<=20000731	USPAT;	2002/05/08
1			US-PGPUB; EPO; JPO;	10:59
			DERWENT;	
			IBM_TDB	
_	86	(438/159).ccls. and @ad<=20000731	USPAT;	2002/05/08
			US-PGPUB;	11:01
			EPO; JPO; DERWENT;	;
			IBM TDB	
_	177	(438/155).ccls. and @ad<=20000731	USPAT;	2002/05/08
			US-PGPUB;	11:03
			EPO; JPO;	
			DERWENT; IBM TDB	
_	139	(257/348).ccls. and @ad<=20000731	USPAT;	2002/05/08
		,,	US-PGPUB;	11:04
			EPO; JPO;	
			DERWENT;	
	173	leurrounding gate transistor!	IBM_TDB USPAT;	2003/02/25
1 -	1/3	'surrounding gate transistor'	USPAT; US-PGPUB;	16:01
			EPO; JPO;	
			DERWENT;	
		40.57 (00.5)	IBM_TDB	0000 (10 (00
_	1842	(257/296).ccls. and @ad<=20000731	USPAT;	2002/10/02
			US-PGPUB; EPO; JPO;	10:31
			DERWENT;	
			IBM_TDB	
-	4811	((257/296) or (257/306) or (257/530) or	USPAT;	2003/02/26
		(257/354) or (438/238-239)).CCLS.	US-PGPUB; EPO; JPO;	09:44
			DERWENT;	
			IBM_TDB	
-	542	((257/296).ccls. and @ad<=20000731) and	USPĀT;	2003/02/26
		'surrounding gate transistor' or 'SGT'	US-PGPUB;	09:42
			EPO; JPO; DERWENT;	
			IBM TDB	
-	166	'surrounding gate transistor' and	USPAT;	2002/10/02
		@ad<=20000731	US-PGPUB;	10:41
			EPO; JPO;	
	1		DERWENT; IBM TDB	
_	87	'gate electrode' with 'electric field	USPAT;	2002/10/04
		effect'	US-PGPUB;	09:59
			EPO; JPO;	
			DERWENT;	
1_	275	 'gate electrode applying'	IBM_TDB USPAT;	2002/10/04
-	2/3	date electione abbiting	US-PGPUB;	10:02
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/10/04
-	39	'gate electrode applying' with 'electric field'	USPAT; US-PGPUB;	2002/10/04
	l	TTETA	EPO; JPO;	10.07
			DERWENT;	
			IBM_TDB	
_	2	'gate electrode applying' with 'electric	USPAT;	2002/10/04
		field' with 'channel'	US-PGPUB; EPO; JPO;	10:10
			DERWENT;	
			IBM TDB	
•	•	·		

	87	leate electrode applicant and telectric	TICDAM.	2002/10/04
_	",	'gate electrode applying' and 'electric field' and 'channel'	USPAT; US-PGPUB;	2002/10/04 10:11
		Titera and Chamier	EPO; JPO;	10.11
			DERWENT;	
			IBM TDB	
_	196	'surrounding gate transistor'	USPAT;	2004/02/24
	-		US-PGPUB;	15:49
			EPO; JPO;	100.15
			DERWENT;	
			IBM TDB	
_	1	"4979014".PN.	USPAT	2003/02/26
	_			09:03
_	1	"5019878".PN.	USPAT	2003/02/26
,				09:03
-	1	"5089870".PN.	USPAT	2003/02/26
				09:04
i –	1	"5115289".PN.	USPAT	2003/02/26
				09:04
-	1	"5163180".PN.	USPAT	2003/02/26
			1	09:06
-	2	("5424227").PN.	USPAT;	2003/02/26
1			US-PGPUB;	09:30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	828	((257/192).CCLS.) and @ad<=20000731	USPAT;	2003/06/16
			US-PGPUB;	15:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB] /
-	46	((257/196).CCLS.) and @ad<=20000731	USPAT;	2003/02/26
			US-PGPUB;	09:35
			EPO; JPO;	
			DERWENT;	
	577	//257/206\ ==1= and Gad<=20000731\ and	IBM_TDB	2003/02/26
-	3//	((257/296).ccls. and @ad<=20000731) and 'surrounding gate transistor' or 'SGT'	USPAT; US-PGPUB;	09:44
		suffounding gate transfistor of 361	EPO; JPO;	09.44
			DERWENT;	
			IBM TDB	
_	23	((257/296).ccls. and @ad<=20000731) and	USPAT;	2003/02/26
		'surrounding gate transistor'	US-PGPUB;	09:44
		Julia dina di	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	5205	((257/296) or (257/306) or (257/530) or	USPAT;	2003/02/26
	1	(257/354) or (438/238-239)).CCLS.	US-PGPUB;	09:49
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	(("5670810") or ("5414287")).PN.	USPĀT;	2003/02/26
			US-PGPUB;	11:04
]			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	"20020011612"	USPAT;	2003/06/16
			US-PGPUB;	15:17
			EPO; JPO;	
			DERWENT;	,
	500		IBM_TDB	2002/06/17
_	506	@ad<=20000731 and 'SGT'	USPAT;	2003/06/17 08:06
			US-PGPUB; EPO; JPO;	00.00
			DERWENT;	
			IBM TDB	
l _	174	@ad<=20000731 and surrounding adj1 gate	USPAT;	2003/06/16
1	• • • • • • • • • • • • • • • • • • •	adj1 transistor	US-PGPUB;	15:41
		···· y	EPO; JPO;	
1			DERWENT;	
			IBM TDB	
	·			

-	70	@ad<=20000731 and 'SGT' and (257/\$).ccls.	USPAT;	2003/06/17
		and (438/\$).ccls.	US-PGPUB;	08:07
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1037	(257/401).ccls. and @ad<=20000731	USPAT;	2003/06/17
			US-PGPUB;	08:23
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	43	(438/284).ccls. and @ad<=20000731	USPAT;	2003/06/17
			US-PGPUB;	08:23
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
_	2	("20020011612").PN.	USPAT;	2004/02/24
		,, ,	US-PGPUB;	15:31
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	("5466621").PN.	USPAT;	2004/02/24
		(5400021 /.IN.	US-PGPUB;	15:31
			EPO; JPO;	13.31
			DERWENT;	
			IBM TDB	
l _	178	 @ad<=20000731 and 'surrounding gate	USPAT;	2004/02/24
	1/6	transistor'	US-PGPUB;	16:46
		Classistor	EPO; JPO;	10:46
			DERWENT;	· .
			IBM TDB	
_	32	'convex semiconductor layer'	USPAT;	2004/02/24
-	32	Convex Semiconductor Tayer	US-PGPUB;	16:40
			EPO; JPO;	10.40
			DERWENT;	
	607	I G C T I	IBM_TDB	2004/02/24
-	687	'SGT'	USPAT;	2004/02/24
			US-PGPUB;	16:41
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/04
-	55	@ad<=20000731 and 'sgt' and 'side wall'	USPAT;	2004/02/24
	1		US-PGPUB;	16:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	